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# Structural and Mechanical Properties of Nanocomposite Nb-Al-N Films

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Nb-Al-N films were deposited by magnetron sputtering of the Nb and Al targets in the Ar-N<sub>2</sub> atmosphere on silicon wafers at various currents supplied to the magnetron device with the Al target (I<sub>Al</sub>=100, 150, 200, 300 mA). The films were studied with XRD, FTIR spectroscopy, as well by nanoindentation and Knoop indentation tests. The films were found to have the nanocomposite nc-B1-NbN<sub>x</sub>/a-AlN structure and exhibit the nanohardness and Knoop hardness in the ranges of 29-33.5 GPa and 46-48 GPa, respectively. The hardness and elastic modulus has an extreme dependence on I<sub>Al</sub>

Keywords: Nb-Al-N films; AlN films; Magnetron sputtering; Film structure; Mechanical properties; Nanoindentation.

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#### 1. INTRODUCTION

NbN-based films exhibit a variety of interesting properties like high hardness and electrical conductivity, thermal stability and chemical inertness [1]. NbN films are used as cathode material for field emission in vacuum microelectronic devices [2]. Nanolayered coatings based on NbN such as TiN/NbN, CrN/NbN, Mo/NbN and W/NbN have been found to show improved mechanical properties as compared to monolayer coatings [2]. Nb-Al-N films were prepared by using various deposition procedures [3-7]. It was shown that the incorporation of Al atoms into the crystal lattice led to the formation of solid solution Nb<sub>1-x</sub>Al<sub>x</sub>N. For Nb<sub>1-x</sub>Al<sub>x</sub>N coatings, the B1 structure was preferable with x below 0.45. In the range of x=0.45-0.71, a mixed B1 and B4 structure was observed, whereas for x>0.71, a B4 structure formed [6,7]. So, the deposited Nb-Al-N films consisted of Nb<sub>1-x</sub>Al<sub>x</sub>N solid solutions with the B1, (seldom  $B_k$ ) and B4 structures, or their mixtures [3-7]. On the other hand, so far, nanocomposite NbN/AlN films were not prepared. Therefore, in the present investigation, we aimed at to deposit nanocomposite Nb-Al-N films on the assumption that the nanocomposite films should exhibit improved mechanical properties as compared to those of Nb<sub>1-x</sub>Al<sub>x</sub>N films.

In the present work, Nb-Al-N films were deposited by magnetron sputtering of the Nb and Al targets at different currents supplied to the magnetron devices with the Al target (I<sub>Al</sub>). The structural and mechanical properties are analyzed depending on values of I<sub>Al</sub>.

## 2. EXPERIMENTAL DETALIES

Nb-Al-N films were deposited on the mirrorpolished Si (100) wafer by DC magnetron sputtering the Nb (99.9%,  $Ø72\times4$  mm) and Nb (99.999%,  $Ø72\times4$ mm) targets in an argon-nitrogen atmosphere at the following deposition parameters: substrate temperature Ts= 350 °C; substrate bias U<sub>B</sub> =-50 V; flow rate (F) F<sub>Ar</sub>=40 sccm; F<sub>N2</sub>=13 sccm; working pressure Pc=0.17 Pa. The current applied to the Al target (I<sub>Al</sub>) was 100, 150, 200 and 300 mA, which corresponded to a discharge power density  $P_{A|}= 5.7$ , 8.6, 11.4, and 17.1 W/cm<sup>2</sup>, respectively. The current on the Nb target ( $I_{Nb}$ ) was 300 mA ( $P_{Nb}=17.1$  W/cm<sup>2</sup>). The base pressure of the vacuum chamber was better than 10<sup>-4</sup> Pa. The distance between the targets and the substrate holder was 8 cm. The dihedral angle between the target planes was ~ 45<sup>o</sup>. The substrates were cleaned ultrasonically before they were put into the vacuum chamber. Also, before deposition, the substrates were etched in the vacuum chamber in hydrogen plasma during 5 min.

The crystal structure of the films was determined by X-ray diffraction (XRD, diffractometer DRON-3M) using  $CuK_{\alpha}$  radiation. The crystallite size in films was evaluated from the broadening of peaks in X-ray diffraction spectra using Scherrer formula. The Fourier transform infrared (FTIR) spectra were measured at room temperature in the range of 400 - 4000 cm<sup>-1</sup> by a spectrometer "FSM 1202" LLC «Infraspek». The hardness and elastic modulus of films were determined from indentation by Nanoindenter-G200 instrument equipped with a Berkovich pyramidal tip under load in the range of 9-13 mN. This range of loads was chosen in order to obtain prominent plastic deformation of film while avoiding the influence of substrate material. The nanohardness (H) and elastic modulus (E) data was obtained from the loaddisplacement curves using the Oliver and Pharr method. The Knoop hardness (HK) was estimated by a Microhardness Tester Micromet 2103 BUEHLER LTD at loading of 100 mN. The thickness of the films was determined with an optical profilometer "Micron-Gamma". The thickness of Nb-Al-N films (d) weakly depends on I<sub>Al</sub>. The values of d was in the range of  $0.7-0.9 \,\mu\text{m}$ .

# 3. RESULTS AND DISCUSSION

In Fig. 1 we show the XRD spectra of the Nb-Al-N films deposited at different I<sub>Al</sub>. Two peaks at  $2\Theta \sim 35.4$ - $36.0^{\circ}$  and  $2\Theta \sim 41.1$ - $41.2^{\circ}$  are identified as the Bl-NbN(111) (35.4°) and Bl-NbN(200) (35.1°) reflections, respectively [038-1155]. A comprehensive analysis shows that the positions of the XRD peaks weakly depend on I<sub>Al</sub>, except those for the film deposited at the highest discharge power at the Al target. For this film,

 $2\Theta = 36^{\circ}$  and  $2\Theta \sim 41.2^{\circ}$  for B1-NbN(111) and B1-NbN(200) reflections, respectively, which indicates the formation Nb<sub>1-x</sub>Al<sub>x</sub>N solid solution. For the sake of comparison, one reminds that the lattice parameters for B1-NbN and B1-AlN are a=4.393 Å and 4.12 Å, respectively [5]. So, the substitution of Nb with Al should lead to shifting the XRD peaks towards high angles, which takes place in the XRD spectrum of the last film.

The average grain size (D) of the films as a function of  $I_{Al}$  is shown in Fig. 2. One can see that the films are nanostructured with the average grain size in the range of 10-21 nm. The value of D reaches a minimum value for the film deposited at  $I_{Al} = 200$  mA.



Fig.  $1-\mbox{XRD}$  spectra of the Nb-Al-N films deposited at various  $I_{\rm Al}$ 



Fig. 2 – Average grain size of Nb-Al-N films as a function of  $I_{\mbox{\scriptsize Al}}.$ 

We have deposited AlN films varying I<sub>Al</sub>. The XRD investigations showed that all AlN films were amorphous (a-AlN) (not shown here). The FTIR spectra of AlN films are shown in Fig. 3. The Al-N network is improved with increasing I<sub>Al</sub>: the band at 667 cm<sup>-1</sup>, associated with the Al-N vibrations [8], becomes more prominent.

Comparing the results presented in Figs 1-3, we aim at a conclusion that the nanocomposite nc-B1-NbN<sub>x</sub>/a-AlN films form at moderate currents  $100 \le I_{Al} \le 200$  mA. The nanocomposite films represent an aggregation of the B1-NbN<sub>x</sub> crystallites embedded into amorphous AlN

matrix. The film deposited at  $I_{Al} > 200$  mA, consist of a  $Nb_{1-x}Al_xN$  solid solution with the cubic structure.

The results of nanoindentation and microindentation of the deposited films are presented in Figs. 4 and 5. It is seen that the nanohardness (H), Knoop hardness (HK) and elastic modulus (E) of Nb-Al-N films are higher than those of NbN and AlN films. Also, the mechanical characteristics of the nanocomposite films are better compared to those of the Nb<sub>1-x</sub>Al<sub>x</sub>N film. We note that Knoop hardness is higher than nanohardness by ~ 50%. This circumstance can be assigned to the fact that nanoindentation occurs at a dynamical regime, whereas, Knoop hardness is determined at a static regime.



Fig. 3 – FTIR spectra of the AlN films deposited at various  $I_{\rm Al}.$ 



Fig. 4 – Nanordness (H) and elastic modulus (E) of the nanocomposite film deposited at  $I_{Al} = 200$  mA (1) in comparison with those of NbN (2) and AlN (3) films, deposited at  $I_{Nb} = 300$ mA and  $I_{Al} = 200$  mA, respectively. The values are presented as functions of indenter penetration.



Fig. 5 – Nanohardness (H), Knoop hardness (HK) and elastic modulus (E) as functions of  $I_{Al}$ .

#### 4. CONCLUSIONS

Nb-Al-N films were deposited by magnetron sputtering the Nb and Al targets at various currents supplied to the magnetron device with the Al target (I<sub>Al</sub>). The films were characterized by XRD, FTIR spectroscopies, as well by means of nano- and microindentations. It was found that the nanocomposite nc-B1-NbN<sub>x</sub>/a-AlN films formed at moderate currents 100  $\leq I_{Al} \leq 200$  mA. At  $I_{Al} > 200$  mA, the film consisted of a Nb<sub>1-x</sub>Al<sub>x</sub>N solid solution with the cubic nanostructure. The nanocomposite coating with the grain size of  $\sim 10$  nm exhibits highest values of H and E. Taking into account the mechanical properties of the deposited nanocomposite films, they can be recommended as wear-resistant and protective coatings.

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